Lecture 5: Beam Dynamics with Space Charge

•In this lecture the concept of emittance compensation is explained for the RF gun using the concept of coordinated plasma oscillations of the slices.

•Beam matching into the booster after the gun following the Ferrario condition is described.

The method of RF compression is explained in conjunction with the tapering of the confining solenoid field to control emittance growth
The concept of generalized dispersion is defined and used to discuss the emittance growth in beam transport due to space charge or CSR.
A simple analytic model is described to compute the emittance growth resulting from various laser produced beam shapes.



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Emittance compensation, Booster matching, Rf compression & <u>Generalized</u> dispersion

Analysis of Space Charge Emittance Growth Due to Shaped Beams

The Seven Laser Shapes



Measure for Each Shape: Projected & Slice Emittance Gain Length FEL Extraction





A Simple Model for the Emittance Growth **Basic Assumptions of Model** Beamlet Line charge density, ho_l 1. Charge is distributed in a regular array of tubes, beamlets. 2. Beamlets see radial space charge force until they overlap. Beam consists of a rectangular array of beamlets, each 3. After overlapping the sc-force becomes small, the electrons driven outward by their radial space charge force are left with radial velocity which becomes emittance. → ~4 r₀ ← Radial electric field outside Area (cell) the tube/beamlet of charge: occupied by each beamlet is: $E_r = \frac{\rho_l}{2\pi\epsilon_0 r} \quad \rho_l = \frac{Q}{N_h l_h} = \frac{16r_0^2 Q}{\pi R^2 l_h} \qquad (4r_0)^2$ $(4r_0)^2$ $N_b = \frac{\pi R^2}{16r^2}$ $E_r = \frac{8}{\pi^2} \frac{Q}{\varepsilon} \frac{r_0^2}{R^2 l_r r}$ Integrate to get energy gain of an electron at radial edge of beamlet: Then the emittance $\mathcal{E}_n = \mathcal{O}_r$ $\frac{p_r^2}{2m} = \frac{8eQr_0^2}{\pi^2 \varepsilon_0 R^2 l_1} \int \frac{dr}{r} = \frac{8eQr_0^2}{\pi^2 \varepsilon_0 R^2 l_1} \ln a$ definition: mcGives the emittance due to the rectangular array of beamlets: Leap of faith: Assume $\langle p_x^2 \rangle \approx \frac{p_r^2}{4}$ $\Delta \varepsilon_n \propto \sigma_x \frac{2r_0}{\pi R} \sqrt{\frac{eQ\ln a}{\varepsilon_m c^2 L}}$



Simple Model Compared to the Expt.

General parameters:

Laser Radius : $R = 0.6mm \implies \sigma_x = 0.3mm$ Bunch Charge : Q = 250 pCBunch Length : $l_b = 6.6 ps = 2mm$ Nominal Emittance : $\varepsilon_{nominal} = 0.45microns$

For 50 mesh pattern: $r_0 = 33 \mu m$

$$\frac{\Delta \varepsilon_n}{\sigma_x} \bigg|_{50mesh} = 5.8microns / mm(rms)$$
$$\Delta \varepsilon_n \bigg|_{50mesh} = 1.7microns$$
$$\varepsilon_n \bigg|_{50mesh} = \sqrt{1.7^2 + 0.45^2} = 1.8microns$$

For 180 mesh, the emittance will be 180/50= 3.6 times smaller: $r_0 = 9 \mu m$

$$\left.\frac{\Delta \varepsilon_n}{\sigma_x}\right|_{180 mesh} = 1.6 microns / mm(rms)$$

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$$\Delta \mathcal{E}_n|_{180mesh} = 0.48microns$$
$$\mathcal{E}_{180mesh} = \sqrt{0.48^2 + 0.45^2} = 0.65microns$$

$$\Delta \varepsilon_n \approx \sigma_x \frac{2r_0}{\pi R} \sqrt{\frac{eQ\ln a}{\varepsilon_0 mc^2 l_b}}$$

$$\boldsymbol{\mathcal{E}}_n = \sqrt{\Delta \boldsymbol{\mathcal{E}}_n^2 + \boldsymbol{\mathcal{E}}_{nominal}^2}$$



GPT Simulation Shows Beamlet Expansion in Early Life of the Beam

50 Mesh Laser Shape

Bagel Laser Shape



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